ABSTRACT

A semiconductor storage device according to the present embodiment includes a first chip including a transistor and a second chip including a memory cell array. The second chip has a first surface bonded to the first chip and a second surface opposite the first surface. A contact extends between the first surface and the second surface and is provided apart from the memory cell array. A first wiring layer is provided above a first end of the contact, which is an end on a second surface side, and is electrically connected to the contact. A first conductive layer is provided between the first end of the contact and the first wiring layer.